



Synthesis of SnO₂ Thin Coatings by Indium and Aluminum Mixed Doping using the Sol-Gel Spin-Coating Technique

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DOI: [10.29303/jppipa.v6i2.391](https://doi.org/10.29303/jppipa.v6i2.391)

Article Info

Received : February 4th, 2020

Revised : May 21th, 2020

Accepted: June 9th, 2020

Abstract: This research succeeded in creating a thin layer of SnO₂ and SnO₂: In+Al through a synthesis process with the sol-gel spin-coating technique on a glass substrate. The manufacture of this thin layer uses the basic material SnCl₂·2H₂O, and the doping material InCl₃·4H₂O and AlCl₃. This thin layer is made with variations in doping concentration, number of layers, and heating temperature. The results of the synthesis of SnO₂: In+Al films show that the thin film formed is more transparent when the doping concentration and the number of layers is increased. Meanwhile, the thin layer that forms is increasingly not transparent when heated at higher temperatures.

Keywords: Thin layer; SnO₂; Indium; Aluminum; Sol-Gel; Spin-Coating.

Citation: Munandar, H., Doyan, A., & Susilawati, S. (2020). Synthesis of SnO₂ Thin Coatings by Indium and Aluminum Mixed Doping using the Sol-Gel Spin-Coating Technique. *Jurnal Penelitian Pendidikan IPA (JPPIPA)*. 6(2), 153-156. doi: <https://doi.org/10.29303/jppipa.v6i2.391>

Introduction

Current technology is developing very rapidly and produces a very small technology, namely nanotechnology. Nanotechnology was introduced by Michael Faraday since 1850 and continues to develop (Battal et al, 2014, Doyan, et al, 2019). One form of nanotechnology is a thin film. The thin layer continues to experience growth both in terms of the way it is made, the materials used, and its application in people's lives (Mak & Shan, 2016). Equipment used by many people uses thin layers, such as LCD TVs, plasma TVs, touch screen handphones (cellphones) and automatic teller machines (ATMs), handheld game consoles, and car navigation systems. In addition, thin films are also used in semiconductor devices such as diodes, capacitors, sensors, and transistors (Anaraki et al, 2016). Thin films can be made from inorganic, organic, metal, metal-organic mixtures, and metal-inorganic mixtures. Thin films have sizes on the nanometer scale (Mihailescu, 2019). Thin films can be as

an insulator, conductor, semiconductor, or superconductor (Mak & Shan, 2016).

Making thin films usually uses materials such as In₂O₃, ITO, SnO₂, TiO₂, WO₃, ZnO (DeAngelis, 2018). SnO₂ is often used as a base for making thin films. This is related to its superiority in nature like its reflectivity, transparency, and low electrical resistance. In addition, SnO₂ thin films have high chemical stability and good transparency properties to light with an energy gap of ~ 3.6 eV (Carvalho et al, 2012). SnO₂ thin film is widely applied in the manufacturing industry of transparent electrodes, solar cells, optical-electrical equipment, and gas sensors. This is based on the cheap price compared to other semiconductors, can to respond to some gases properly, has a long service life, and only requires simple electronic devices in the implementation of sensing. In addition, the properties of SnO₂ are very dependent on the crystallographic quality and surface morphology of deposited layers (Morales et al, 2015). Experimental results show that materials such as TiO₂, ZnO, and SnO₂ are proven capable of detecting O₂, CO,

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and several types of hydrocarbon gases (Mishra et al, 2017).

Pure or doped SnO₂ thin films have been produced through various techniques, such as sol-gel spin coating to synthesize SnO₂ thin films with Aluminum doping (Doyan et al, 2017), pyrolysis spray to synthesize SnO₂ thin films with Fluorine doping (Bakr et al, 2016), synthesis of SnO₂ by doping Fluorine using the sol-gel spin-coating technique (Susilawati et al, 2019), and sol-gel dip coating to synthesize the SnO₂ thin layer (Carvalho et al, 2012). The synthesis of SnO₂ doped Indium thin films tends to be more transparent when the doping concentration is increased and will become less transparent when the heating temperature is increased (Hakim et al, 2019). The effect of the addition of aluminum doping concentrations on the quality of transparency of SnO₂ thin-film was also proven to increase the level of transparency (Imawanti et al, 2017).

This study will use the sol-gel spin coating technique because it has several advantages, namely having a short crystallization process, the use of low temperatures, nanoparticles, pure yields, economic and simple in nature (Yati et al, 2017; Doyan et al, 2019). Some of the variables involved in the sol-gel spin coating technique are solution concentration, doping concentration, rotational speed, turnaround time, solution aging time, layer repetition, and heat treatment (Doyan et al, 2017).

Method

The basic material used as a coating in this study was 0.902 grams of Tin (II) chloride dihydrate (SnCl₂·2H₂O with a molar mass of 225.63 grams/mol, 98% purity, Merck). The solvent uses 40 ml of ethanol (C₂H₅OH) with a molar mass of 46.07 gram/mol, 98% purity, Merck) at room temperature. The ingredients for doping are 0.4266; 0.8532; 1.2797; 1.7063; and 2.1329 grams In+Al. The substrate used is glass with a size of 10 mm x 10 mm x 3 mm. Other supporting materials are aquades water, detergent soap, and alcohol which are used to clean substrates. SnO₂: In+Al thin film synthesis includes substrate preparation, sol-gel manufacturing, thin-film manufacturing, and the heating process.

Substrate preparation is done by washing the glass substrate using detergent soap, then stirring using a shaker for 30 minutes. After that, rinse it using distilled water, and soak it using alcohol for 30 minutes. Then heat it using the furnace for one hour at 100 °C (Doyan and Humaini, 2017).

Making sol-gel is done by mixing SnCl₂·2H₂O with InCl₃·4H₂O and AlCl₃ with a mixture

concentration of 1 M, so as to produce SnO₂ sol-gel doped with Indium and Aluminum with different concentrations. Comparison of SnO₂:In+Al concentrations in this thin layer is 100:0%, 95:5%, 90:10%, 85:15%, 80:20%, 75:25%. After mixing, the ingredients are stirred using a magnetic stirrer to produce a homogeneous solution. After stirring, the solution is allowed to stand for 24 hours.

Making thin films is done by the sol-gel spin-coating technique using a spin coater. SnO₂: In+Al solution is dropped on a glass substrate, then rotated using a spin coater at 2000 rpm for 2 minutes. Samples were made as many as 120 samples, with variations in doping concentration, number of layers, and heating temperature. After all, samples have been rotated, they are stored at different temperatures, namely room temperature, 50 °C, 100 °C, 150 °C, and 200 °C. Each sample at this temperature amounted to 24 samples.

Result and Discussion

The process of making SnO₂: In+Al thin films consists of the stages of substrate preparation, sol-gel manufacturing, thin-film manufacturing, and the heating process. The substrate used is glass. The glass is washed first to ensure the glass is clean of other substances. After that, the glass is heated to vaporize the remnants of other substances attached to the glass.

The next step is the process of making sol-gel by mixing SnCl₂·2H₂O with InCl₃·4H₂O and AlCl₃ with a mixture concentration of 1 M using ethanol solvent. The amount of ethanol used as a solvent is 20 ml (Muliyadi et al, 2019). The amount of SnCl₂·2H₂O, InCl₃·4H₂O, and AlCl₃ dissolved in 20 ml of ethanol in order to obtain the desired concentration ratio can be seen in Table 1. The results of the SnO₂: In+Al solution formed by the sol-gel technique can be seen in Figure 1.



Figure 1. SnO₂: In+Al solution with different doping concentrations.

Table 1. Comparison of mass composition of thin film SnO₂:In+Al

SnO ₂ :In+Al (%)	SnCl ₂ .2H ₂ O (gram)	InCl ₃ .4H ₂ O (gram)	AlCl ₃ (gram)
100 : 0	4.5125	0.0000	0.0000
95 : 5	4.2869	0.1466	0.0667
90 : 10	4.0613	0.2932	0.1335
85 : 15	3.8356	0.4398	0.2000
80 : 20	3.6100	0.5865	0.2667
75 : 25	3.3844	0.7331	0.3334

The next process is the manufacture of thin films using spin-coating techniques. The glass substrate is placed on a spin coater, then drops of SnO₂: In+Al solution. Glass substrate that has been dropped by SnO₂: In+Al solution is rotated at 2000 rpm for 2 minutes. This screening is intended so that the SnO₂: In+Al solution is spread evenly on the glass substrate.

After all, samples have been rotated, the process of adding layers and heating the samples at different temperatures is carried out. It aims to determine the effect of many layers and heating temperature on the quality of the thin film formed. Previous research has proven that the concentration of doping Indium (Hakim et al, 2019) and Aluminum doping (Imawanti et al, 2017) and different heating temperatures have an effect on the quality of the thin film formed. In other research, it has been proven that the more concentration of doping Aluminium and Zinc which is added to SnO₂, the more transparency of the thin films which is produced (Ikraman et al, 2017, Doyan et al, 2017).

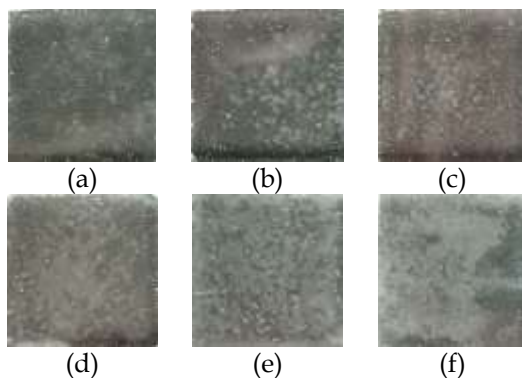


Figure 2. SnO₂:In+Al thin film at 50 °C with 3 layers in various SnO₂:In+Al concentrations (a) 75:25%, (b) 80:20%, (c) 85:15%, (d) 90:10%, (e) 95:5%, (f) 100:0%.

Figure 2 shows that the SnO₂: In+Al thin films from the picture (a) to picture (f) experience a decreasing level of transparency. This shows that SnO₂: In+Al thin films with higher doping concentrations have higher transparent levels.

The number of layers in a thin layer also affects the transparency level of the thin film. The results of

the synthesis of SnO₂: In+Al thin films with different amounts of layers can be seen in Figure 3.

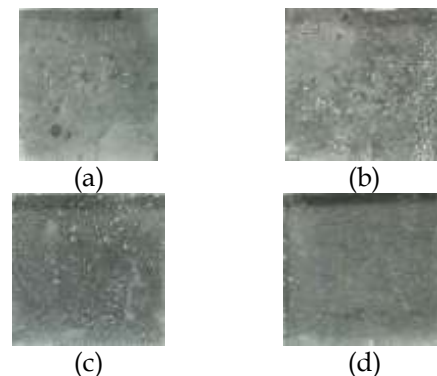


Figure 3. SnO₂:In+Al thin layer at 100 °C with a concentration of SnO₂:In+Al = 95:5% with variations in the number of layers (a) 1, (b) 2, (c) 3, (d) 4.

Figure 3 shows that the SnO₂: In+Al thin film formed is more transparent when the number of layers is added. This proves that the number of layers in the thin layer has an effect on the level of transparency.

In addition to doping concentration and the number of layers, the heating temperature also affects the transparency quality of the formed SnO₂: In+Al films. The results of the synthesis of thin films at different temperatures can be seen in Figure 4.

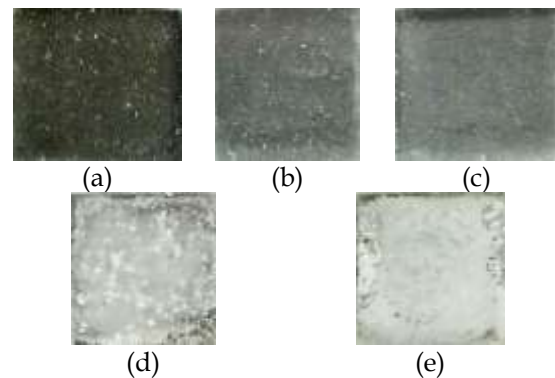


Figure 4. SnO₂:In+Al thin film with the 4 layers with a SnO₂ concentration: In+Al = 95:5% at temperature (a) room temperature, (b) 50 °C, (c) 100 °C, (d) 150 °C, (e) 200 °C.

Figure 4 shows that from the picture (a) to picture (e) the SnO₂: In+Al thin layer is becoming less transparent. This shows that the addition of the heating temperature makes the SnO₂: In+Al thin layer more transparent.

Conclusion

The process of making sol-gel can take place normally at room temperature. The sol-gel spin-coating technique is good and efficient for making thin-film samples. The thin film produced by the sol-gel spin-

coating technique has good surface properties. The surface quality of SnO₂: In+Al films produced is influenced by doping concentration, the number of layers, and heating temperature. The more concentration and the number of layers makes the level of transparency of the thin layer higher. Meanwhile, the thin layer becomes less transparent when the heating temperature is increased.

Acknowledgements

My best thanks for my lecturers who have guided me in finishing this research. Thank you to the Master of Science Education Program, Postgraduate University of Mataram which always facilitates the administration of this research. Furthermore, thank you to the Ministry of research and technology of higher education who have provided research funding assistance through the Student Thesis Research scheme along with the research of the supervisor so that this thesis can be completed.

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